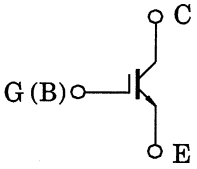
TOSHIBA IGBT Module Silicon N Channel IGBT

MG75J1BS11

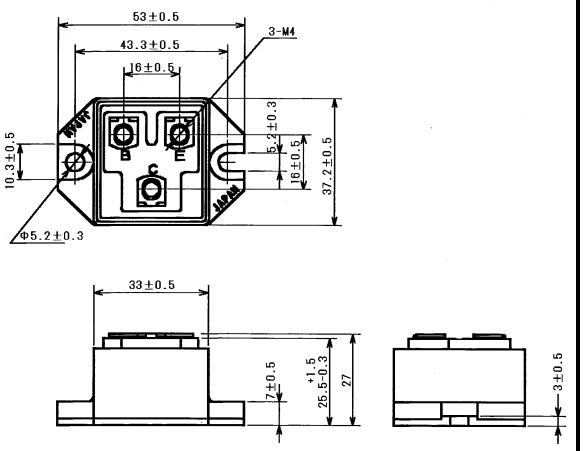
High Power Switching Applications
Motor Control Applications

- Enhancement-mode
- The electrodes are isolated from case.

Equivalent Circuit



Unit: mm

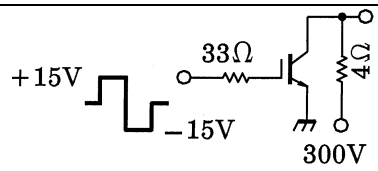


JEDEC	—
JEITA	—
TOSHIBA	2-33F2A

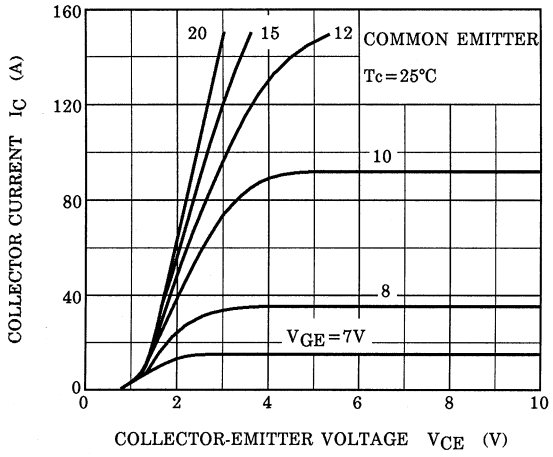
Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C	75	A
	1ms	I_{CP}	150	
Collector power dissipation		P_C	200	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−40 to 125	°C
Isolation voltage		V_{Isol}	2500 (AC 1 minute)	V
Screw torque (Terminal / mounting)		—	2 / 3	N·m

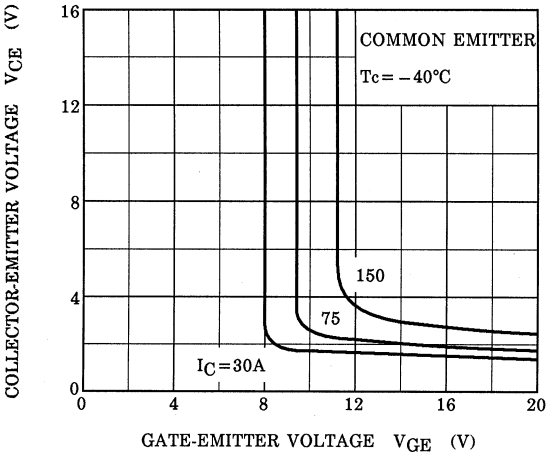
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	V_{GE} = ±20V, V_{CE} = 0	—	—	±500	nA
Collector cut-off current		I_{CES}	V_{CE} = 600V, V_{GE} = 0	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE\ (OFF)}$	I_C = 75mA, V_{CE} = 5V	3.0	—	6.0	V
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 75A, V_{GE} = 15V	—	2.3	2.7	V
Input capacitance		C_{ies}	V_{CE} = 10V, V_{GE} = 0, f = 1MHz	—	6000	—	pF
Switching time	Rise time	t_r		—	0.3	0.8	μs
	Turn-on time	t_{on}		—	0.4	0.8	
	Fall time	t_f		—	0.6	1.0	
	Turn-off time	t_{off}		—	1.0	1.6	
Thermal resistance		$R_{th(j-c)}$	—	—	—	0.6	°C / W

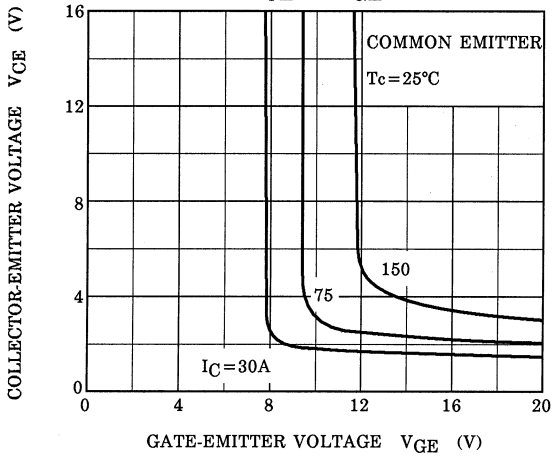
I_C – V_{CE}



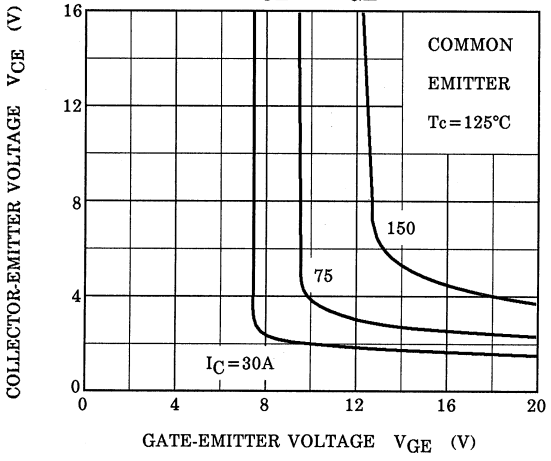
V_{CE} – V_{GE}



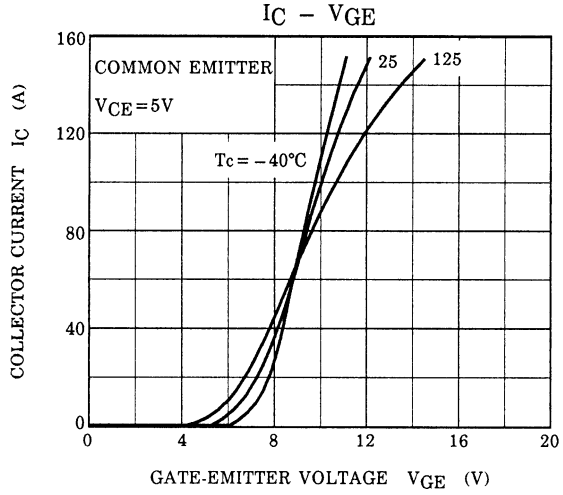
V_{CE} – V_{GE}



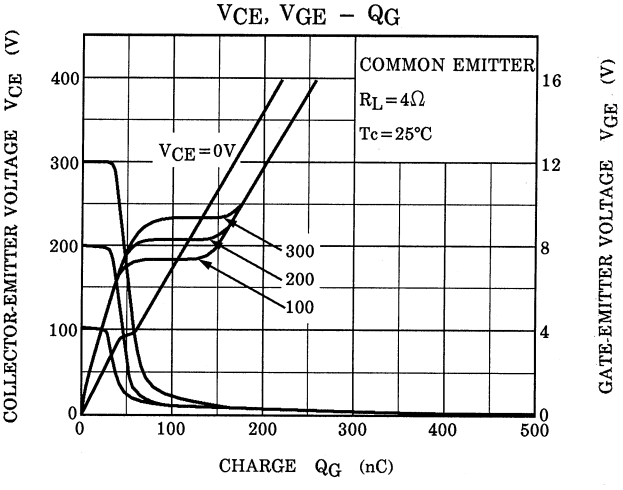
V_{CE} – V_{GE}



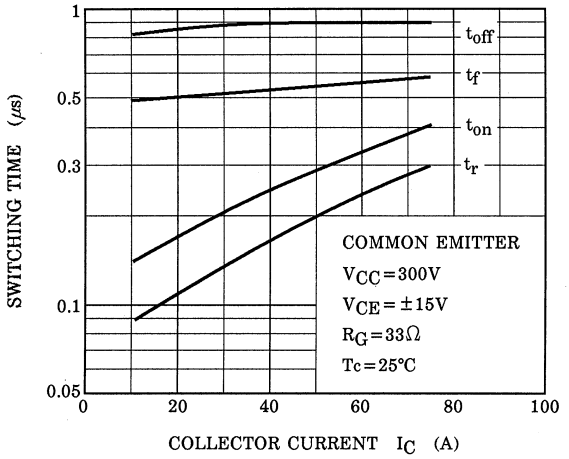
I_C – V_{GE}



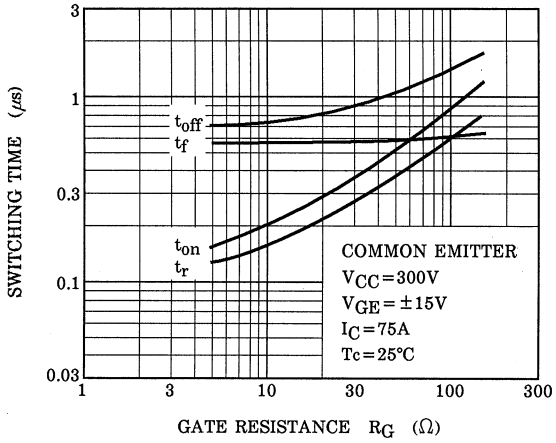
V_{CE}, V_{GE} – Q_G



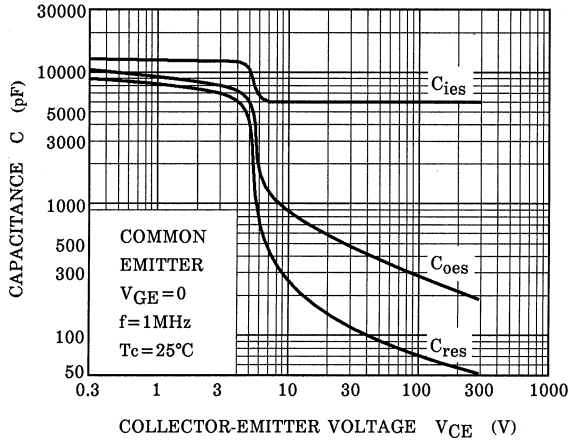
SWITCHING TIME – I_C



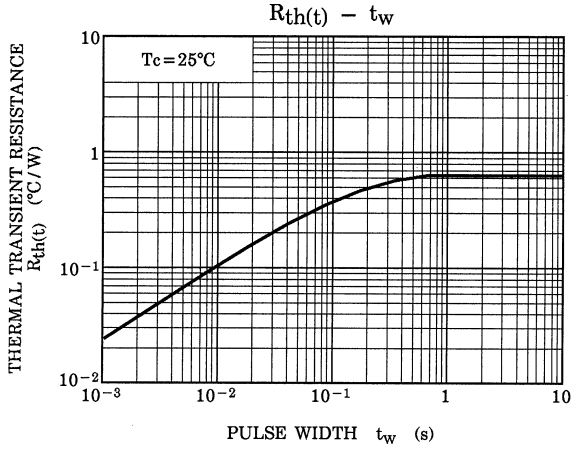
SWITCHING TIME – R_G



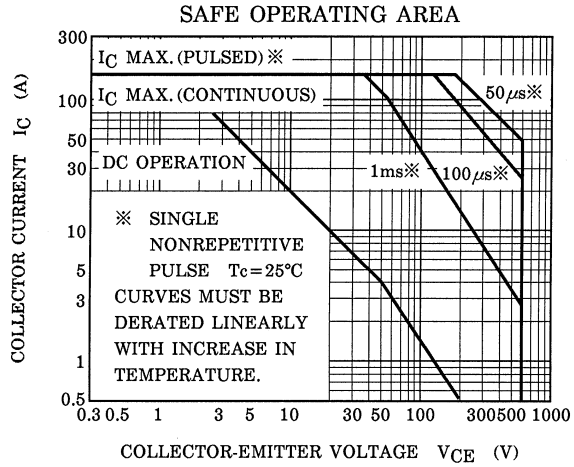
C – V_{CE}



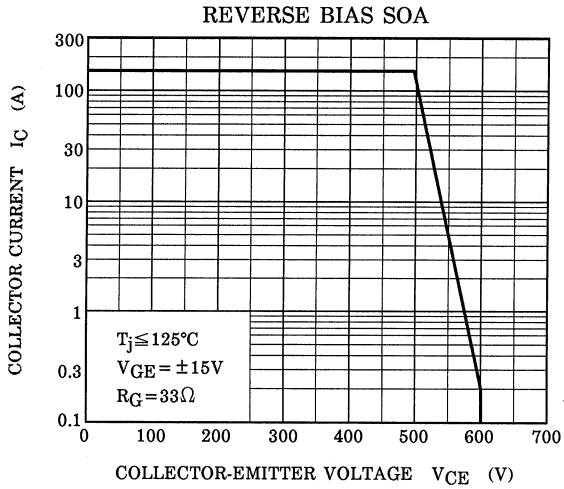
$R_{th(t)}$ – t_w



SAFE OPERATING AREA



REVERSE BIAS SOA



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